

LAPT

2SA1295

勝特力材料 886-3-5753170
 勝特力电子(上海) 86-21-34970699
 勝特力电子(深圳) 86-755-83298787
[Http://www.100y.com.tw](http://www.100y.com.tw)

Silicon PNP Epitaxial Planar Transistor (Complement to type 2SC3264)

Application : Audio and General

■Absolute maximum ratings (Ta=25°C)

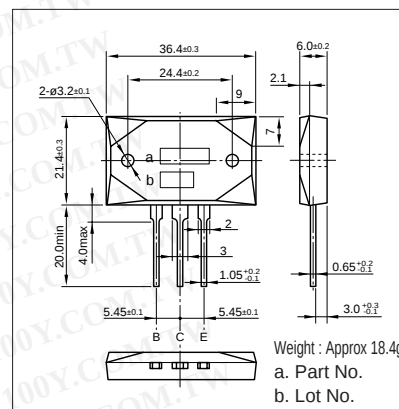
Symbol	Ratings	Unit
V _{CB0}	-230	V
V _{CEO}	-230	V
V _{EB0}	-5	V
I _C	-17	A
I _B	-5	A
P _C	200(T _C =25°C)	W
T _J	150	°C
T _{stg}	-55 to +150	°C

■Electrical Characteristics (Ta=25°C)

Symbol	Conditions	Ratings	Unit
I _{CB0}	V _{CB} =-230V	-100max	μA
I _{EB0}	V _{EB} =-5V	-100max	μA
V _{(BR)CEO}	I _C =-25mA	-230min	V
h _{FE}	V _{CE} =-4V, I _C =-5A	50min*	
V _{CE(sat)}	I _C =-5A, I _B =-0.5A	-2.0max	V
f _r	V _{CE} =-12V, I _E =2A	35typ	MHz
C _{OB}	V _{CB} =-10V, f=1MHz	500typ	pF

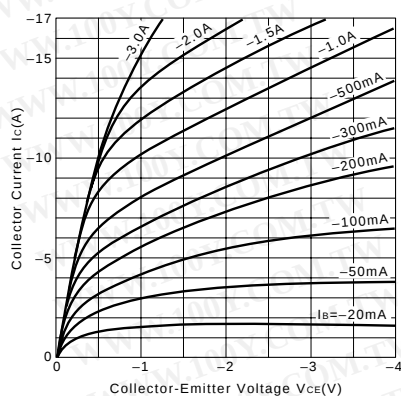
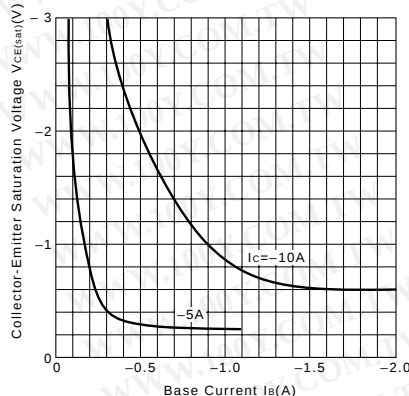
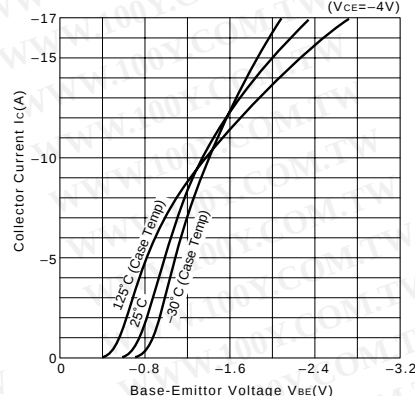
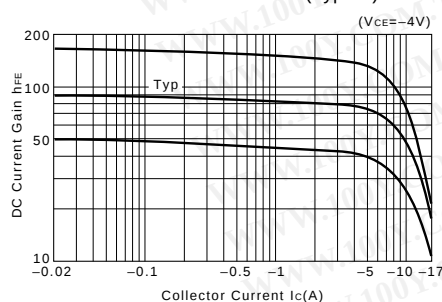
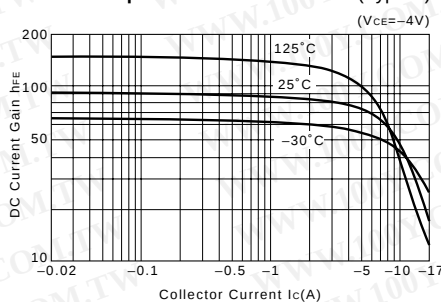
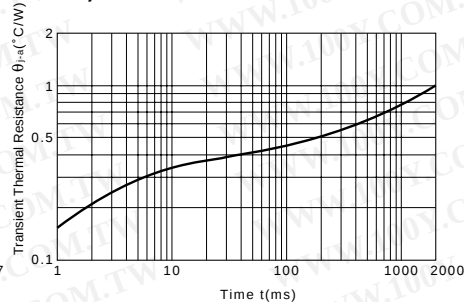
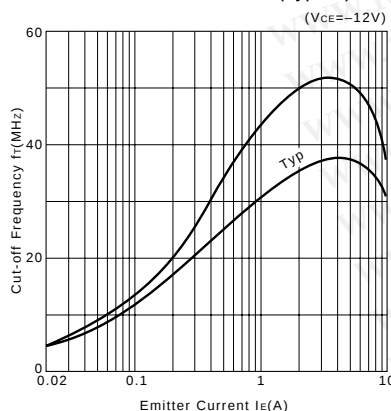
*h_{FE} Rank O(50to100), Y(70to140)

External Dimensions MT-200

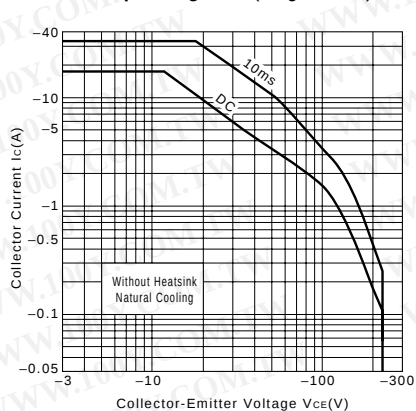
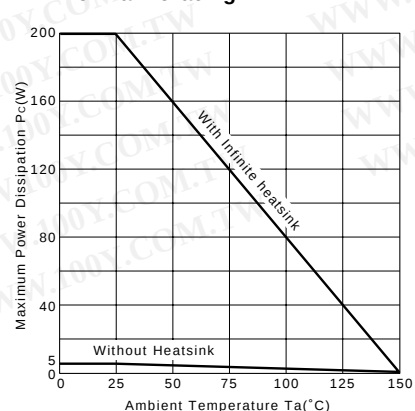


■Typical Switching Characteristics (Common Emitter)

V _{CC} (V)	R _L (Ω)	I _C (A)	V _{BB1} (V)	V _{BB2} (V)	I _{B1} (mA)	I _{B2} (mA)	t _{on} (μs)	t _{stg} (μs)	t _f (μs)
-60	12	-5	-10	5	-500	500	0.35typ	1.50typ	0.30typ

I_C-V_{CE} Characteristics (Typical)V_{CE(sat)}-I_B Characteristics (Typical)I_C-V_{BE} Temperature Characteristics (Typical)h_{FE}-I_C Characteristics (Typical)h_{FE}-I_C Temperature Characteristics (Typical)θ_{JA}-t Characteristicsf_T-I_E Characteristics (Typical)

Safe Operating Area (Single Pulse)

P_C-T_a Derating

Silicon NPN Epitaxial Planar Transistor (Complement to type 2SA1295)

Application : Audio and General Purpose

■Absolute maximum ratings (Ta=25°C)

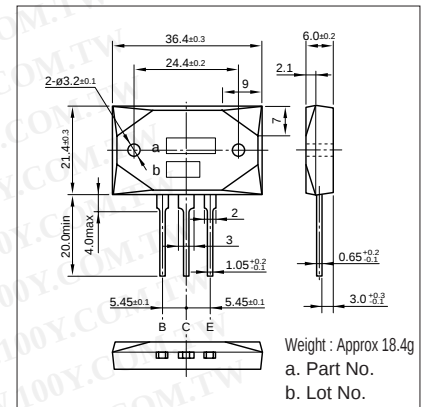
Symbol	Ratings	Unit
V _{CB0}	230	V
V _{CE0}	230	V
V _{EB0}	5	V
I _C	17	A
I _B	5	A
P _C	200(T _C =25°C)	W
T _J	150	°C
T _{stg}	-55 to +150	°C

■Electrical Characteristics (Ta=25°C)

Symbol	Conditions	Ratings	Unit
I _{CB0}	V _{CB} =230V	100max	μA
I _{EB0}	V _{EB} =5V	100max	μA
V(BR) _{CEO}	I _C =25mA	230min	V
h _{FE}	V _{CE} =4V, I _C =5A	50min*	
V _{CE(sat)}	I _C =5A, I _B =0.5A	2.0max	V
f _T	V _{CE} =12V, I _E =-2A	60typ	MHz
COB	V _{CB} =10V, f=1MHz	250typ	pF

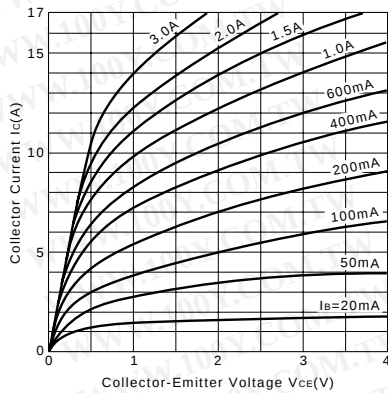
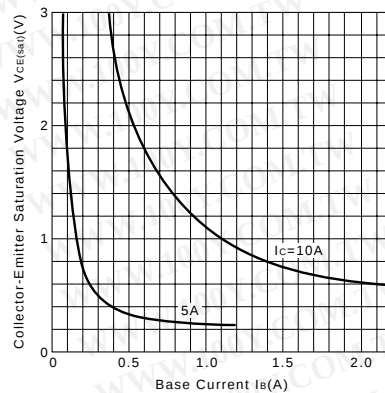
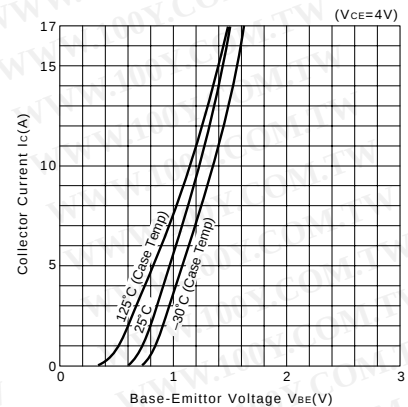
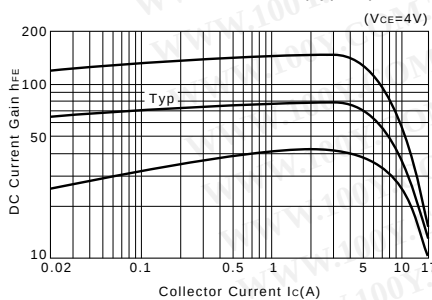
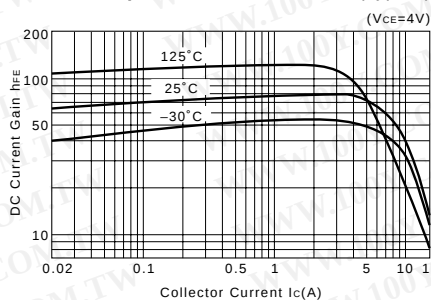
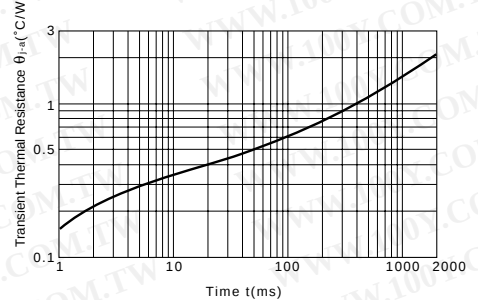
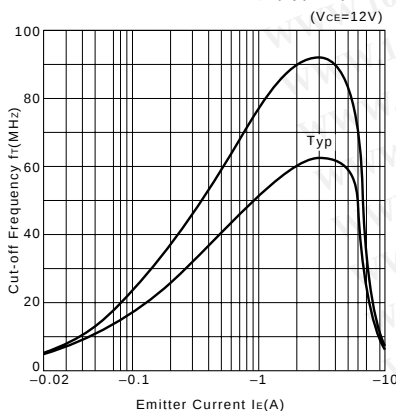
*h_{FE} Rank ○(50 to 100), Y(70 to 140)

External Dimensions MT-200

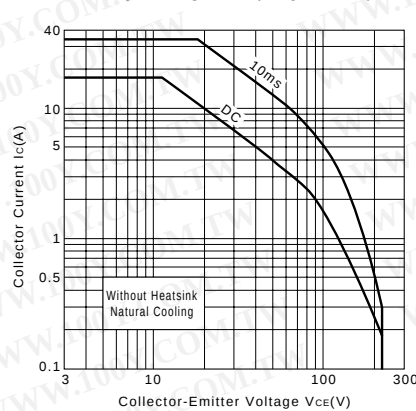


■Typical Switching Characteristics (Common Emitter)

V _{CC} (V)	R _L (Ω)	I _C (A)	V _{BB1} (V)	V _{BB2} (V)	I _{B1} (A)	I _{B2} (A)	t _{on} (μs)	t _{stg} (μs)	t _f (μs)
60	12	5	10	-5	0.5	-0.5	0.30typ	2.40typ	0.50typ

I_C-V_{CE} Characteristics (Typical)V_{CE(sat)}-I_B Characteristics (Typical)I_C-V_{BE} Temperature Characteristics (Typical)h_{FE}-I_C Characteristics (Typical)h_{FE}-I_C Temperature Characteristics (Typical)θ_{J-A}-t Characteristicsf_T-I_E Characteristics (Typical)

Safe Operating Area (Single Pulse)

P_C-T_a Derating